



SANYO Semiconductors

DATA SHEET

LV5212VH — Bi-CMOS IC 8ch LED Driver

Overview

The LV5212VH is a semiconductor integrated circuit that incorporates a serial input and serial or parallel output 8-stage shift register that features a CMOS structure based on Bi-CMOS process technology. The LV5212VH also contains an n-channel CMOS construction high-withstand-voltage, large-current drive 8-stage parallel output driver.

Features

- Serial input and serial or parallel output
- Serial output enables cascade connection
- Serial input/output levels compatible with typical CMOS devices
- High-withstand-voltage LED driver with open drain output
 - High withstand voltage ($V_{DS} < 50V$)
 - High-current drive ($I_O \text{ max} = 300mA$)
- Operating temperature range $T_a = -25$ to $75^\circ C$
- Enable input for output control
- Low supply current ($0.0\mu A$ typ. during standby)

Specifications

Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	$V_{CC \text{ max}}$	SV_{CC}	6	V
Output voltage	$V_O \text{ max}$	LEDO1 to LEDO8 off	50	V
Output current	$I_O \text{ max}$		300	mA
Allowable power dissipation	$P_d \text{ max}$	$T_a \leq 25^\circ C$ *	1000	mW
Operating temperature	T_{opr}		-25 to +75	$^\circ C$
Storage temperature	T_{stg}		-40 to +125	$^\circ C$

* Specified board : 114.3mm × 76.1mm × 1.6mm, glass epoxy board.

* The device must be used within the ranges warranted for its specifications so as to ensure its specified ratings (such as maximum ratings and operating condition ranges) are not exceeded even momentarily.

Use of the device in such a way that its ratings are exceeded may cause failures, damage and other problems.

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Operating Conditions at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage	V_{CC}	SV_{CC}	5.0	V
Operating supply voltage range	$V_{CC\ op}$	SV_{CC}	3.0 to 5.5	V
Output applied voltage	V_O		50	V
Output current	I_O	Duty = 45% to 55%	300	mA

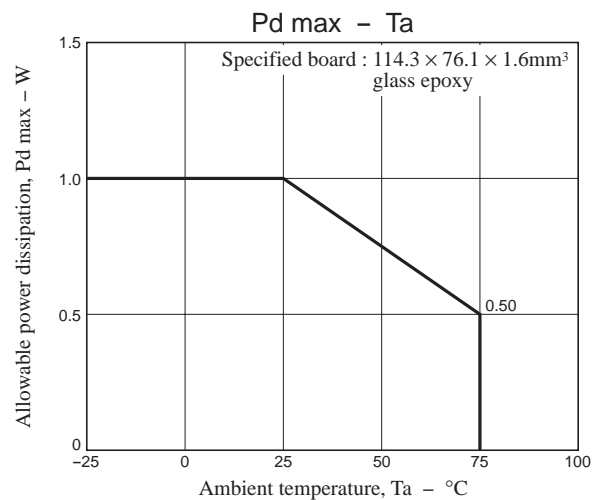
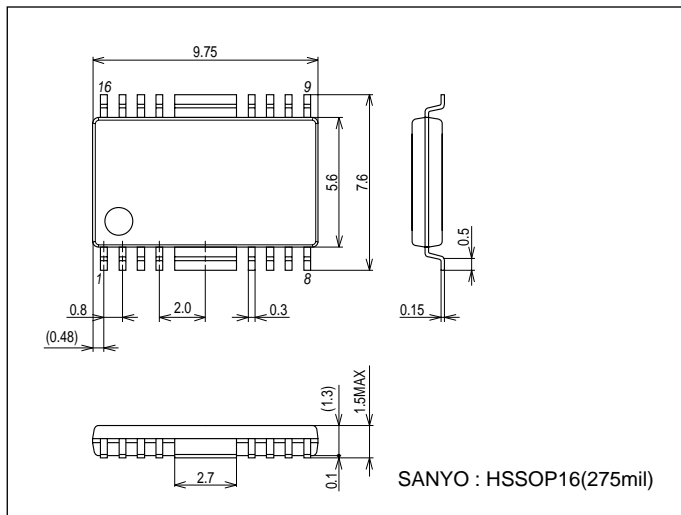
Electrical Characteristics at $T_a = 25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Quiescent current drain	I_{CC1}	LEDO driver off (standby)		0	5	μA
LEDO output on resistance	R_{on}	$I_O = 100\text{mA}$		3		Ω
OFF leak current	I_{leak}	$V_O = 50\text{V}$		0	10	μA
Control circuit block						
H level 1	V_{INH1}	Input H level	$V_{CC} \times 0.8$			V
L level 1	V_{INL1}	Input L level	0		$V_{CC} \times 0.2$	V
H level 2	V_{OUTH1}	SOUT $I_O = -1\text{mA}$	$V_{CC} - 0.3$			V
L level 2	V_{OUTL1}	SOUT $I_O = 1\text{mA}$	0		0.3	V

Package Dimensions

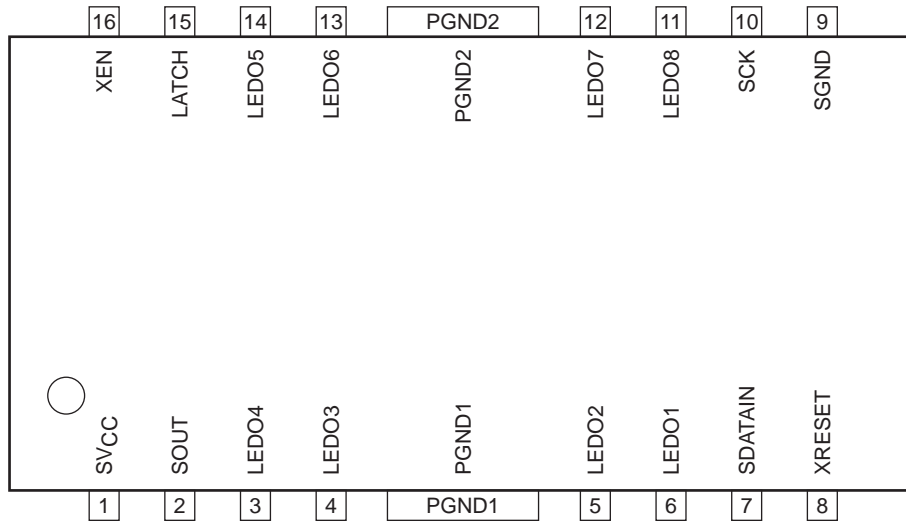
unit : mm (typ)

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Pin Assignment

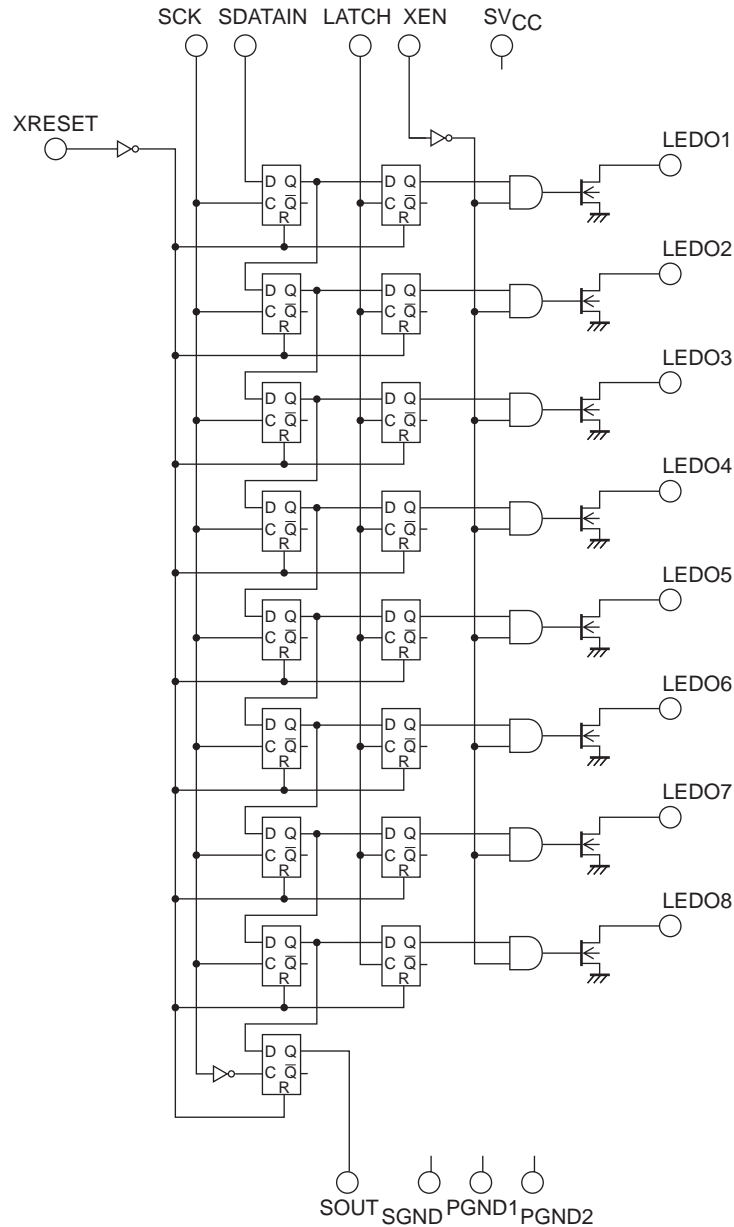


Top view

Pin Descriptions

Pin No.	Pin name	I/O	Description
1	SV _{CC}		Power supply
2	SOUT	O	shift register output (final-stage shift register)
3	LEDO4	O	LEDO4 Latch output (LEDO4 of shift register)
4	LEDO3	O	LEDO3 Latch output (LEDO3 of shift register)
5	LEDO2	O	LEDO2 Latch output (LEDO2 of shift register)
6	LEDO1	O	LEDO1 Latch output (LEDO1 of shift register)
7	SDATAIN	I	Serial input
8	XRESET	I	Reset input (shift register and latch)
9	SGND		GND
10	SCK	I	Clock input (for shift register)
11	LEDO8	O	LEDO8 Latch output (LEDO8 of shift register)
12	LEDO7	O	LEDO7 Latch output (LEDO7 of shift register)
13	LEDO6	O	LEDO6 Latch output (LEDO6 of shift register)
14	LEDO5	O	LEDO5 Latch output (LEDO5 of shift register)
15	LATCH	I	Latch input When the latch input is held low, the LED0 output status is retained. When a high-level is input, the LED0 outputs change when the status of the shift register changes.
16	XEN	I	Enable inputs (LEDO1 to LEDO8) When a high-level is input, all the LED0 outputs are turned off. When a low-level is input, the shift register data is output to LED0.
PGND1	PGND1		GND
PGND1	PGND2		GND

Block Diagram



Function

The LV5212VH consists of 1) an 8-stage D-type flip-flop and 2) an 8-stage D-type flip-flop connected to the output of 1). When data is supplied to the serial data input (SDATAIN) and the clock pulse is supplied to the clock input (SCK), the serial data input signal is input to the internal shift register and the data already in the shift register shifted sequentially when the clock changes from low to high.

The serial output (SOUT) is used to connect multiple LV5212VH to expand the number of bits and is connected to the SDATAIN of the next stage. (Cascade connection supported.)

For parallel output, when the output control enable input (XEN) is low, the latch input (LATCH) changes from low to high and the clock pulse input changes from low to high, the serial data input signal is output to LEDO1, and the output is shifted sequentially. For parallel outputs (LED2 to LED8), the signals whose polarities inverted from those of the serial data input (SDATAIN) are output.

When the EN input is high, outputs LED01 through LED01 all turn off.

When the reset input is low, outputs LED01 through LED8 and SOUT outputs all turn off. The power must be turned on after checking that the reset input is low.

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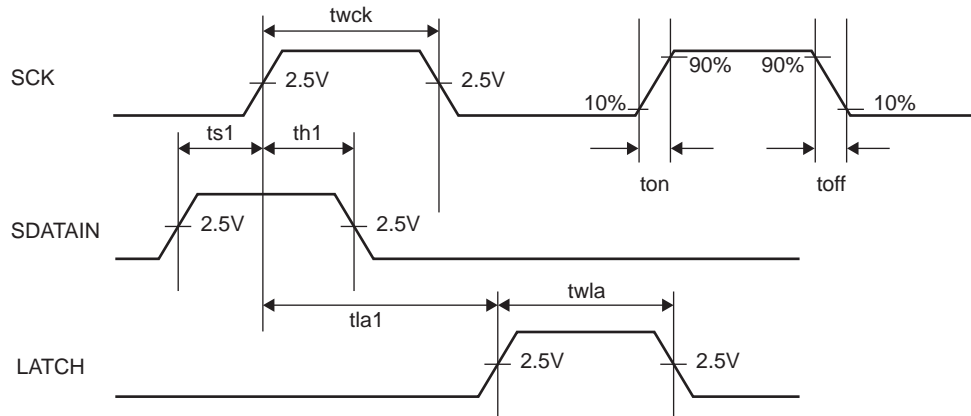
Pin Functions

Pin No.	Pin Name	Pin function	Equivalent Circuit
7 10	SDATAIN SCK	Pull-down input	<p>The circuit shows a pull-down resistor connected to the pin and SGND. Protection diodes are connected from the pin to SVCC and SGND. The internal CMOS input structure is also shown.</p>
8 15 16	XRESET LATCH XEN	Pull-up input	<p>The circuit shows a pull-up resistor connected to the pin and SVCC. Protection diodes are connected from the pin to SVCC and SGND. The internal CMOS input structure is also shown.</p>
2	SOUT	SOUT output	<p>The circuit shows a CMOS driver stage with an output diode connected to SVCC and the other terminal to SGND.</p>
3 4 5 6 11 12 13 14	LEDO4 LEDO3 LEDO2 LEDO1 LEDO8 LEDO7 LEDO6 LEDO5	LEDO outputs LEDO1 to LEDO8	<p>The circuit shows a CMOS driver stage with an output diode connected to SVCC and the other terminal to PGND.</p>

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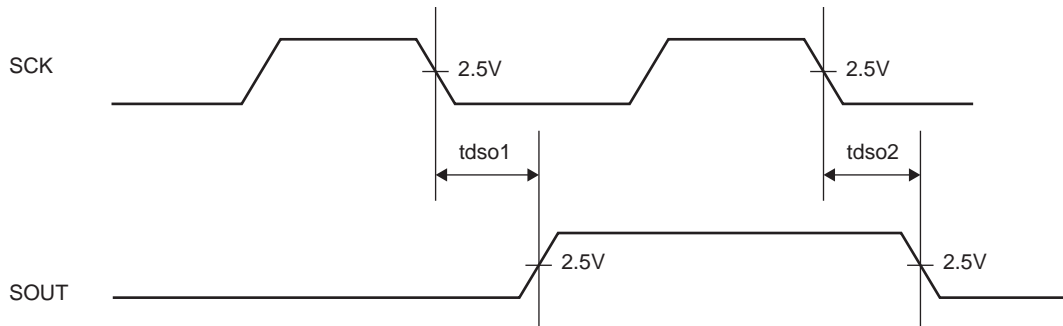
Timing conditions

Parameter	symbol	Conditions	min	typ	max	unit
Clock frequency	fs1	SCK Duty = 50%			10	MHz
Clock pulse width	twck	SCK	50			ns
Latch pulse width	twla	LATCH	50			ns
Data set up time	ts1	SDATAIN setup time relative to the rise of SCK	25			ns
Data hold time	th1	SDATAIN data hold time relative to the rise of SCK	25			ns
Clock latch time	tla1		100			ns
Input conditions 1	ton	SCK and SDATAIN rise time			100	ns
Input conditions 2	toff	SCL and SDATAIN fall time			100	ns



SOUT output timings

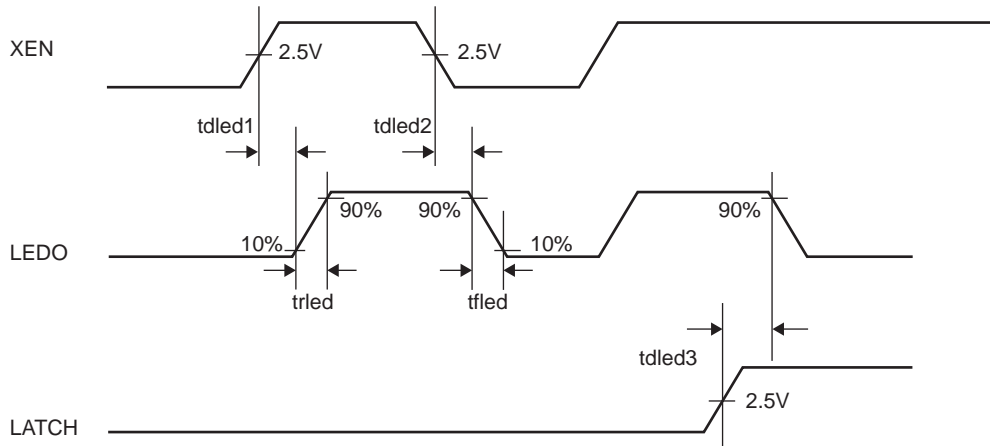
Parameter	symbol	Conditions	min	typ	max	unit
SOUT delay time 1	tdso1	The time from a SCK falling edge to SOUT rising edge			50	MHz
SOUT delay time 2	tdso2	The time from a SCK falling edge to SOUT falling edge			50	ns



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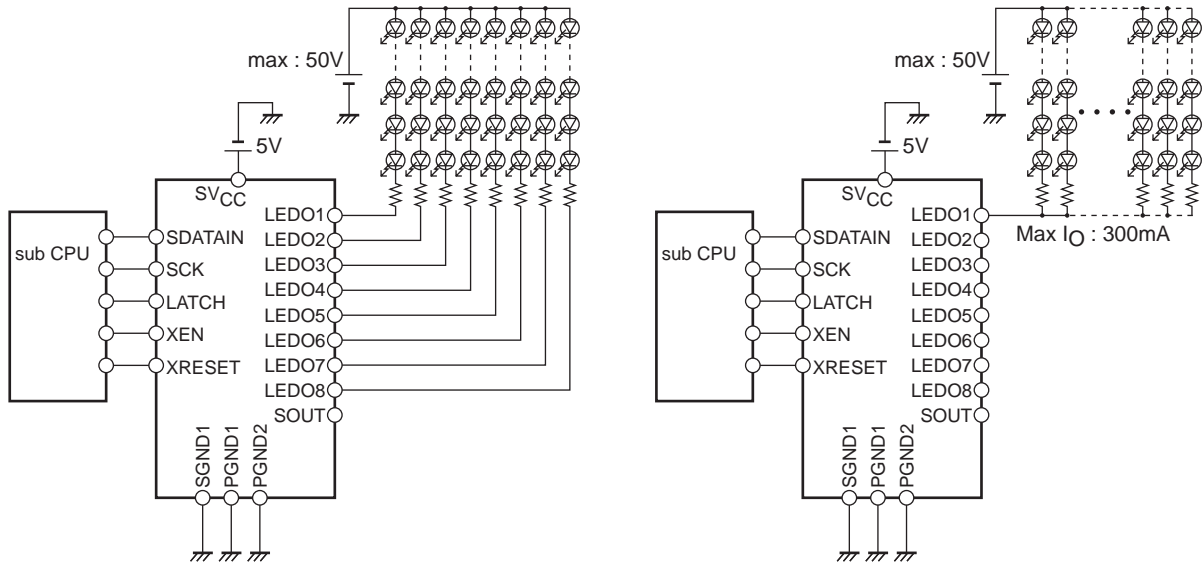
LEDO output timings

Parameter	symbol	Conditions	min	typ	max	unit
LEDO delay time 1	tdled1	The time from an XEN rising edge to LEDO rising edge CL = 30pF, I _O = 100mA, V _O = 30V		100		ns
LEDO delay time 2	tdled2	The time from an XEN falling edge to LEDO falling edge CL = 30pF, I _O = 100mA, V _O = 30V		100		ns
LEDO rise time	trled	LEDO rise time CL = 30pF, I _O = 100mA, V _O = 30V		200		ns
LEDO fall time	tfled	LEDO fall time CL = 30pF, I _O = 100mA, V _O = 30V		200		ns
LEDO delay time 3	tdled3	The time from a LATCH rising edge to LEDO falling edge CL = 30pF, I _O = 100mA, V _O = 30V		200		ns

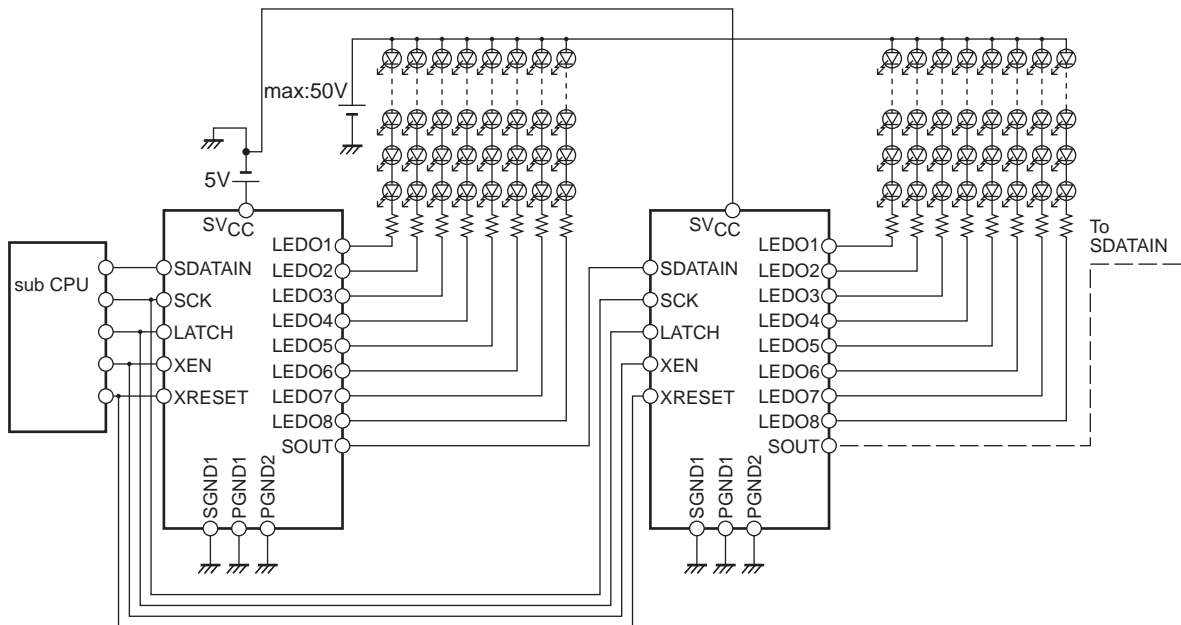


Application Circuit Example

- When parallel output is used

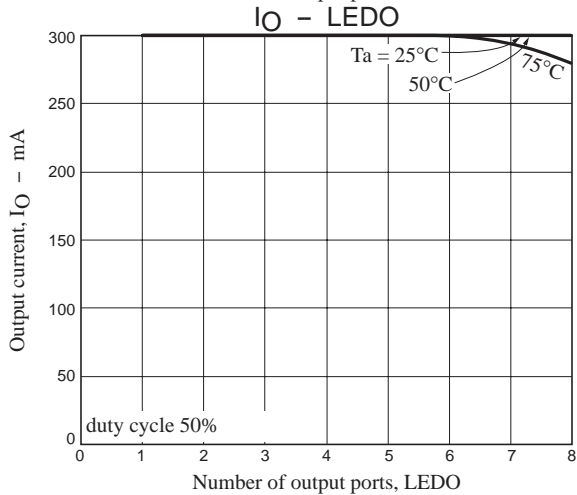
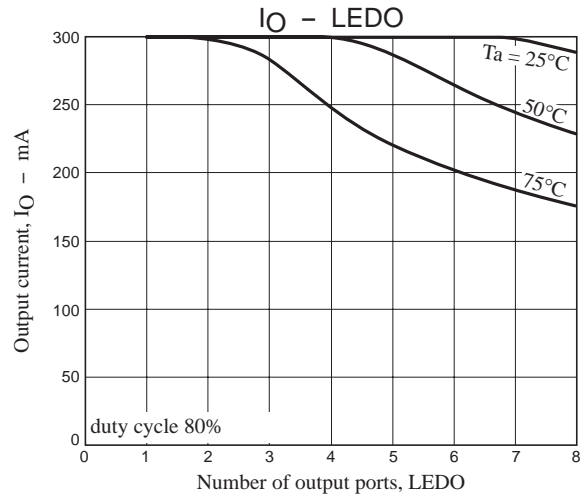
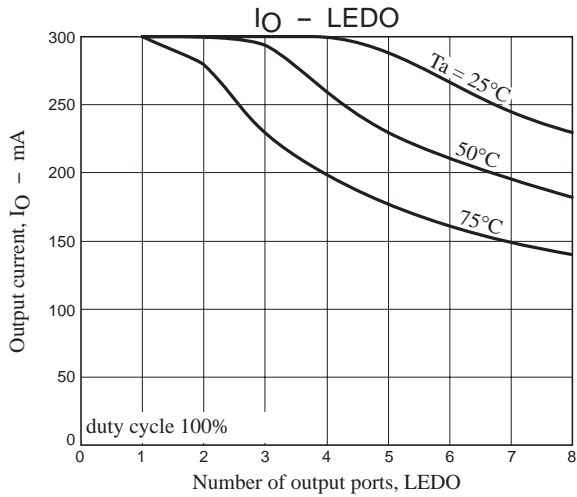


- When serial output is used (SOUT cascade connection)



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Allowable output current characteristics



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